

Supporting information

Fluid Guided CVD Growth for Large-scale Monolayer Two-dimensional Materials

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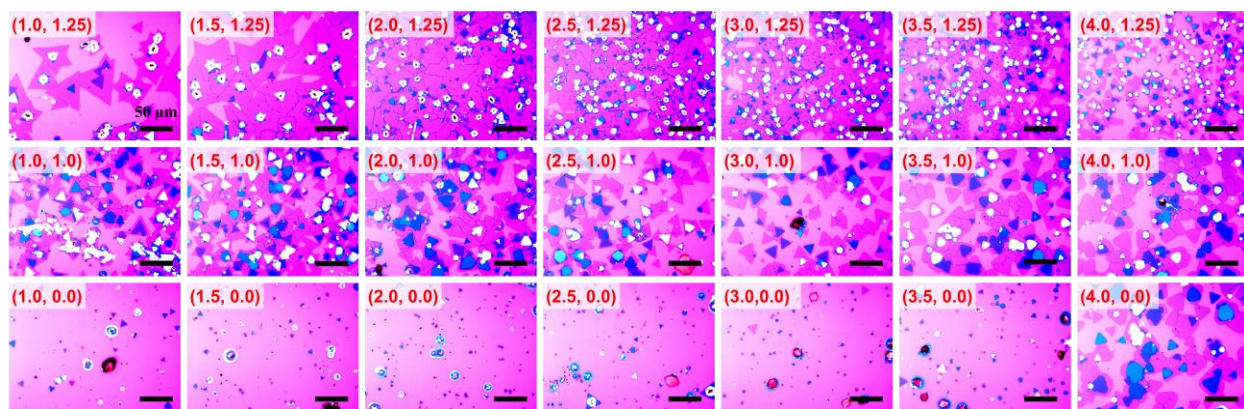


Figure S1. The detailed morphology distribution over the substrate using the standard APCVD.

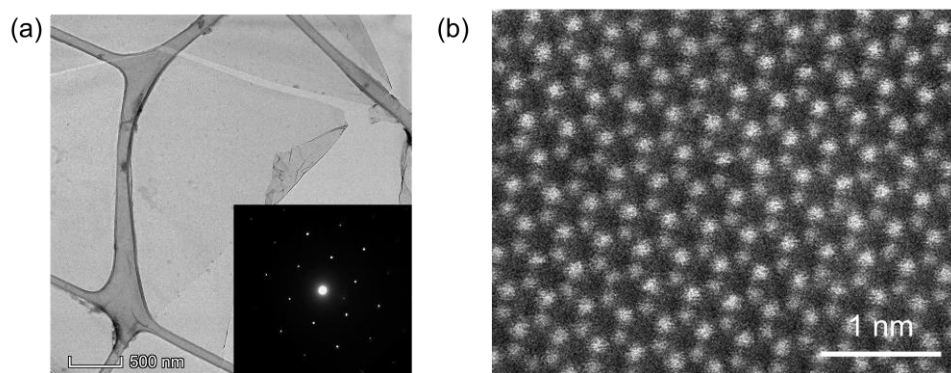


Figure S2. (a) TEM image of monolayer MoSe₂ with inset selected area electron diffraction pattern and (b) annular dark field STEM image of monolayer MoSe₂.

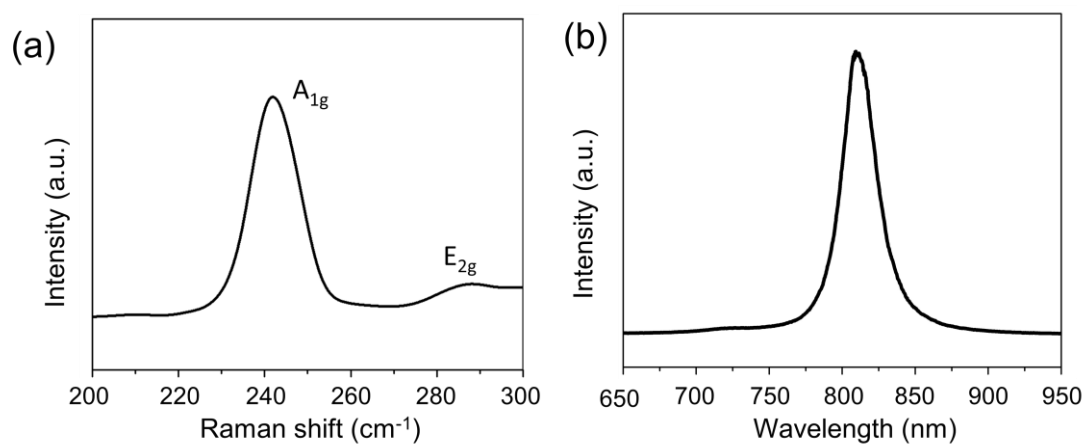


Figure S3. The Raman (a) and PL(b) spectra of the monolayer MoSe₂.

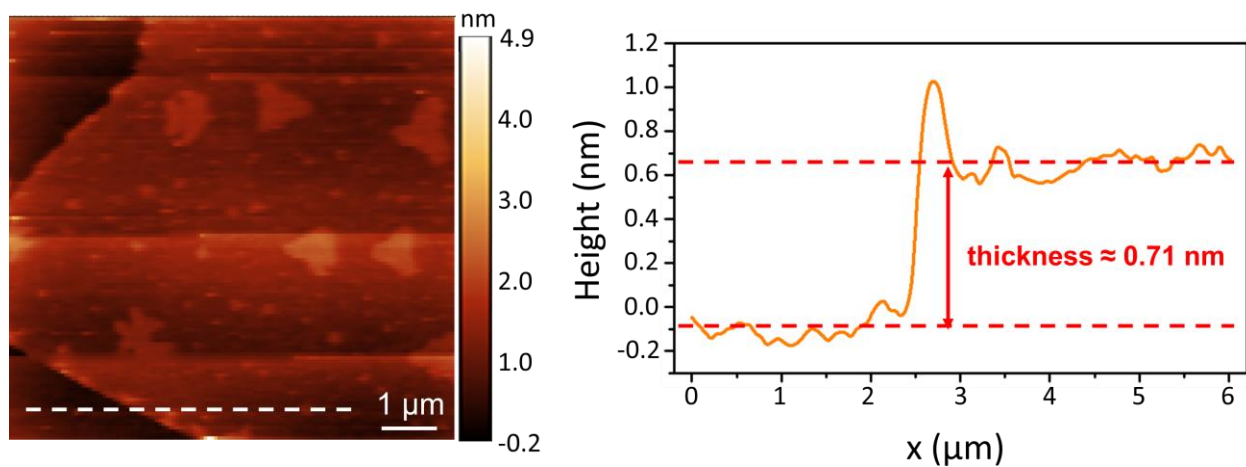


Figure S4. Atomic force microscope (AFM) topography of the monolayer MoSe₂ flakes.

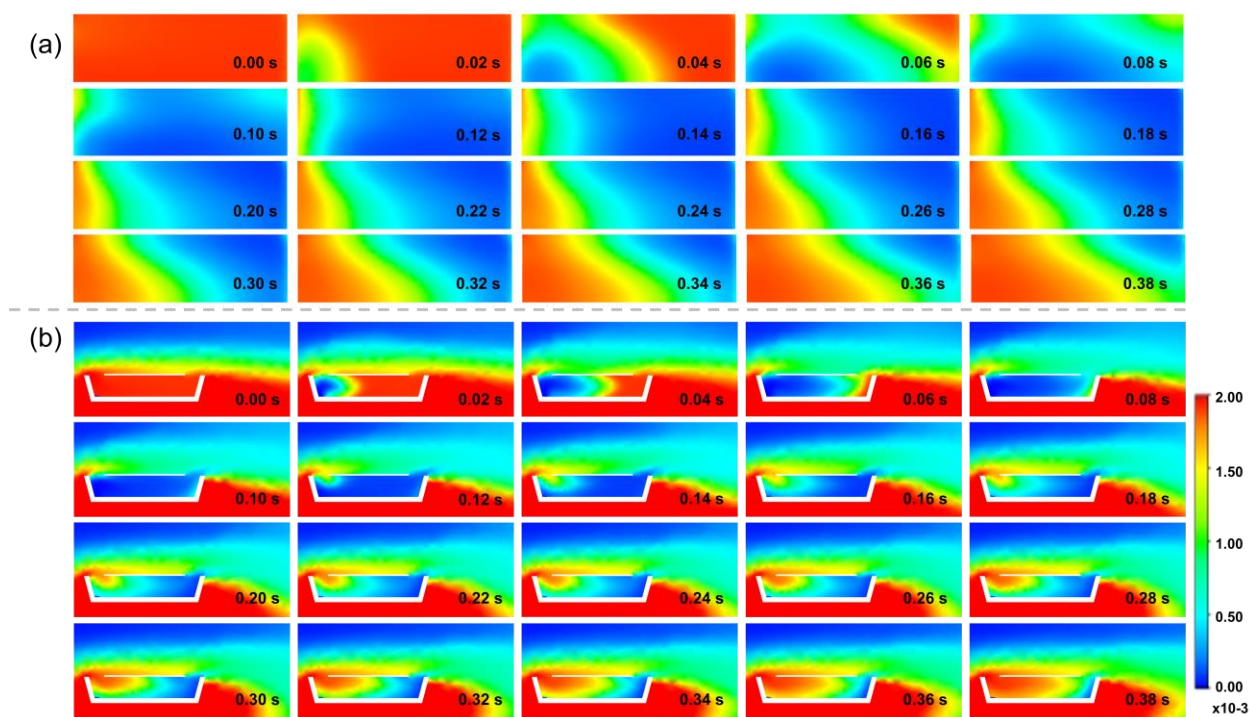


Figure S5. Se concentration evolution in the standard APCVD growth process. (a) top view, (b) cross-sectional view.

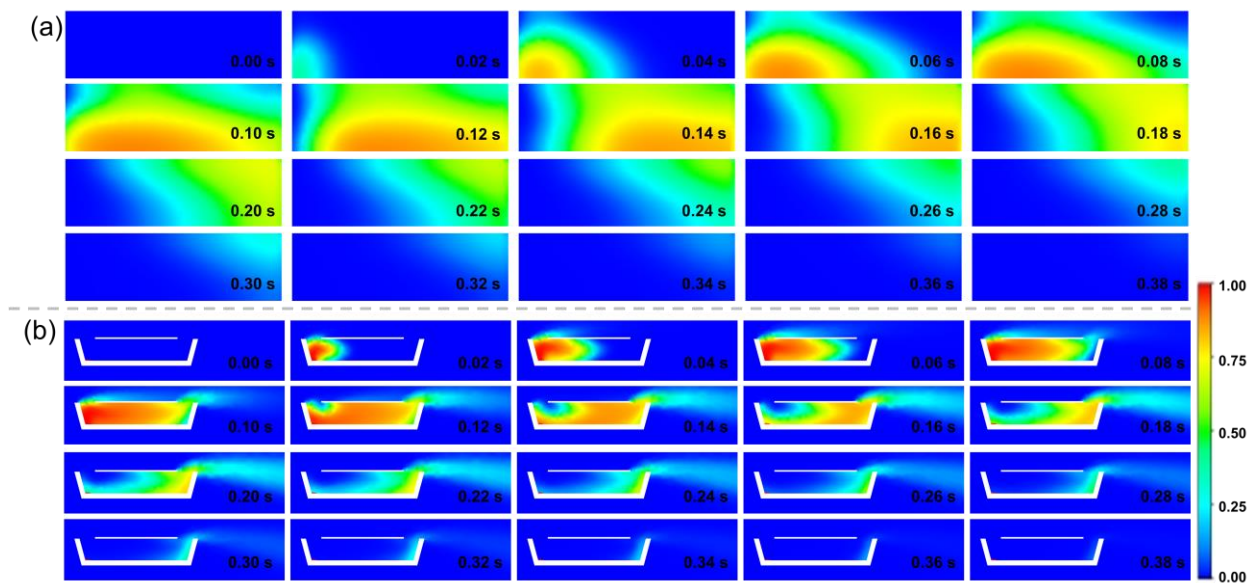


Figure S6. MoO_3 concentration evolution in the standard APCVD growth process. (a) top view, (b) cross-sectional view.

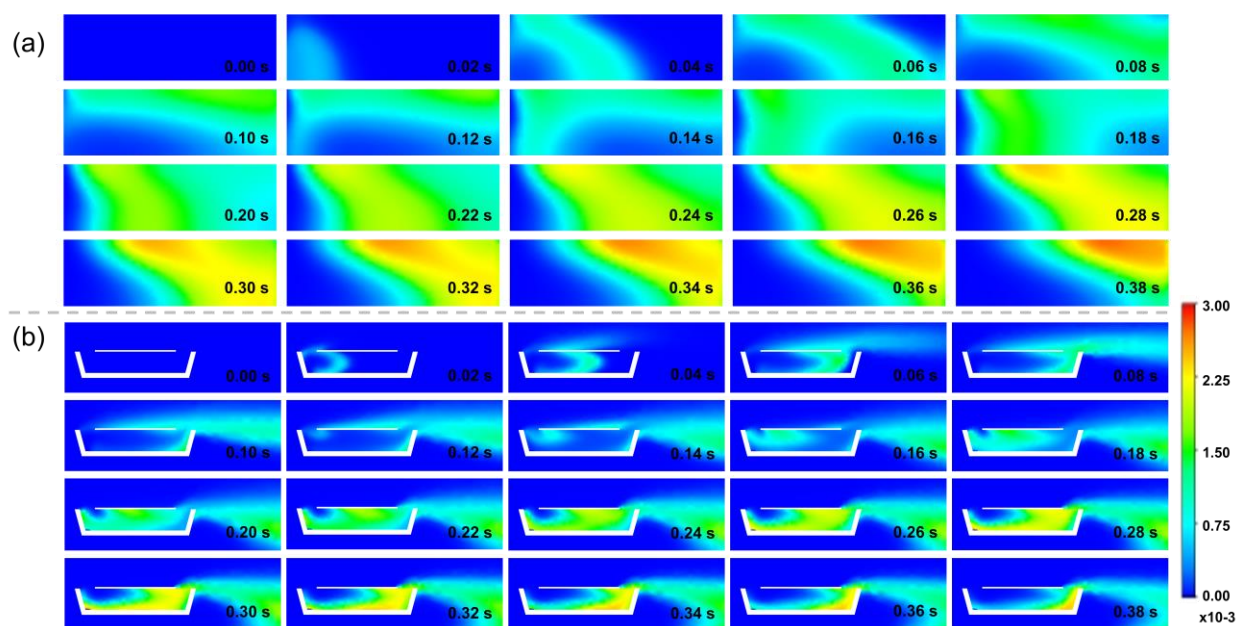


Figure S7. MoSe_2 concentration evolution in the standard APCVD growth process. (a) top view, (b) cross-sectional view.

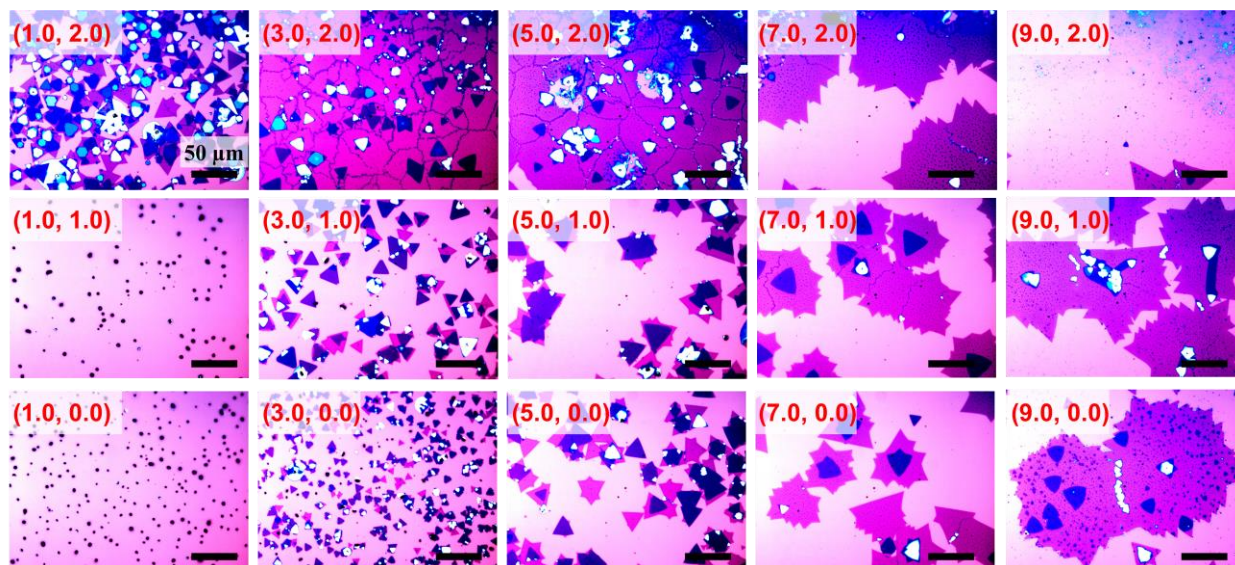


Figure S8. The detailed morphology distribution over the substrate using the flipped APCVD.

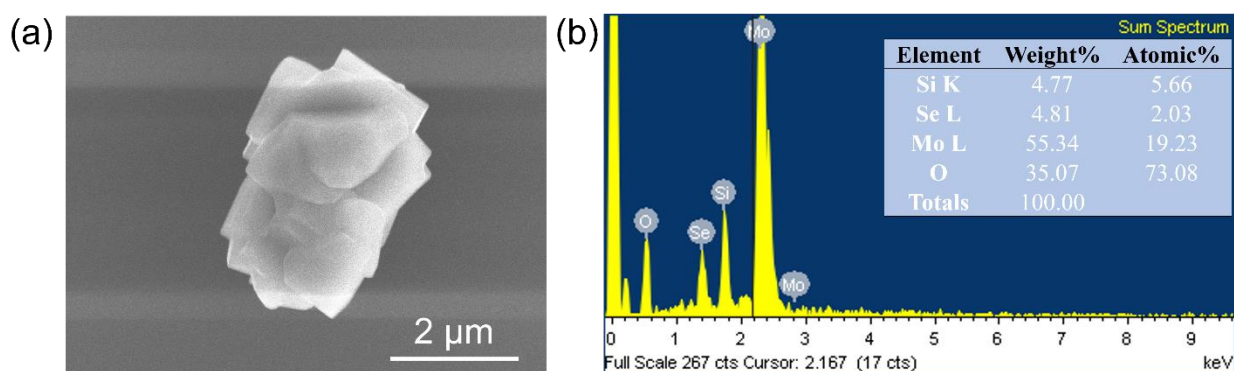


Figure S9. (a) The SEM image of deposited particles. (b) The Energy-dispersive X-ray spectroscopy (EDX) analysis of (a).

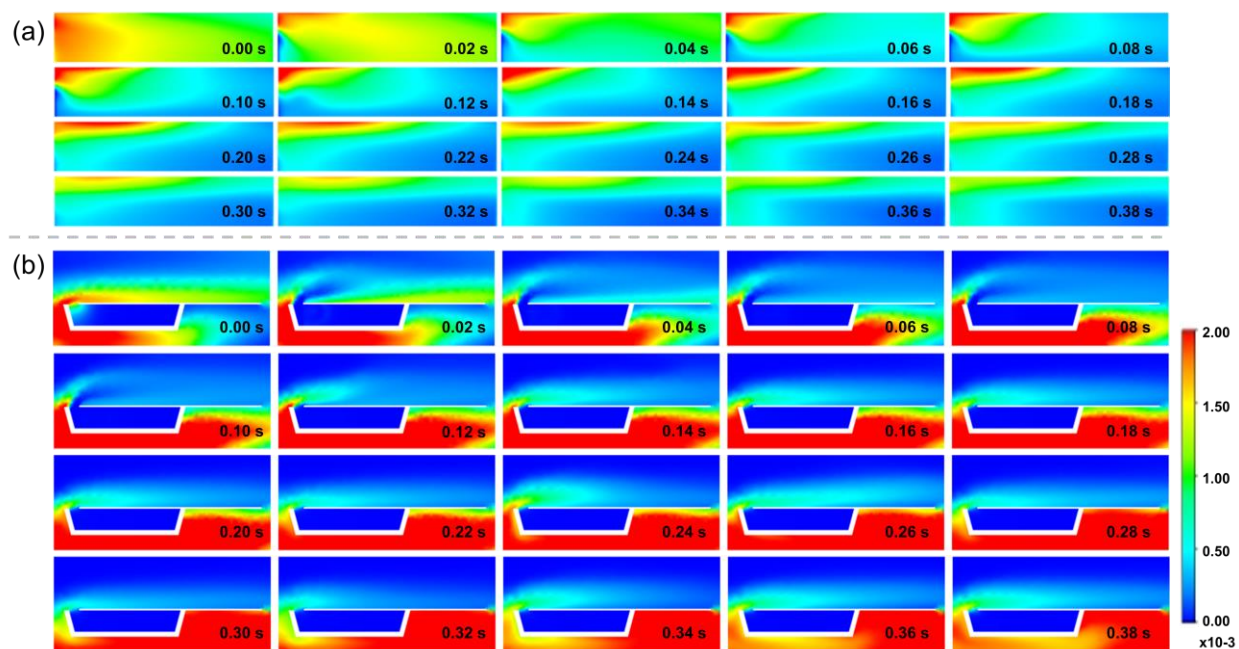


Figure S10. Se concentration evolution in the flipped APCVD growth process. (a) top view, (b) cross-sectional view.

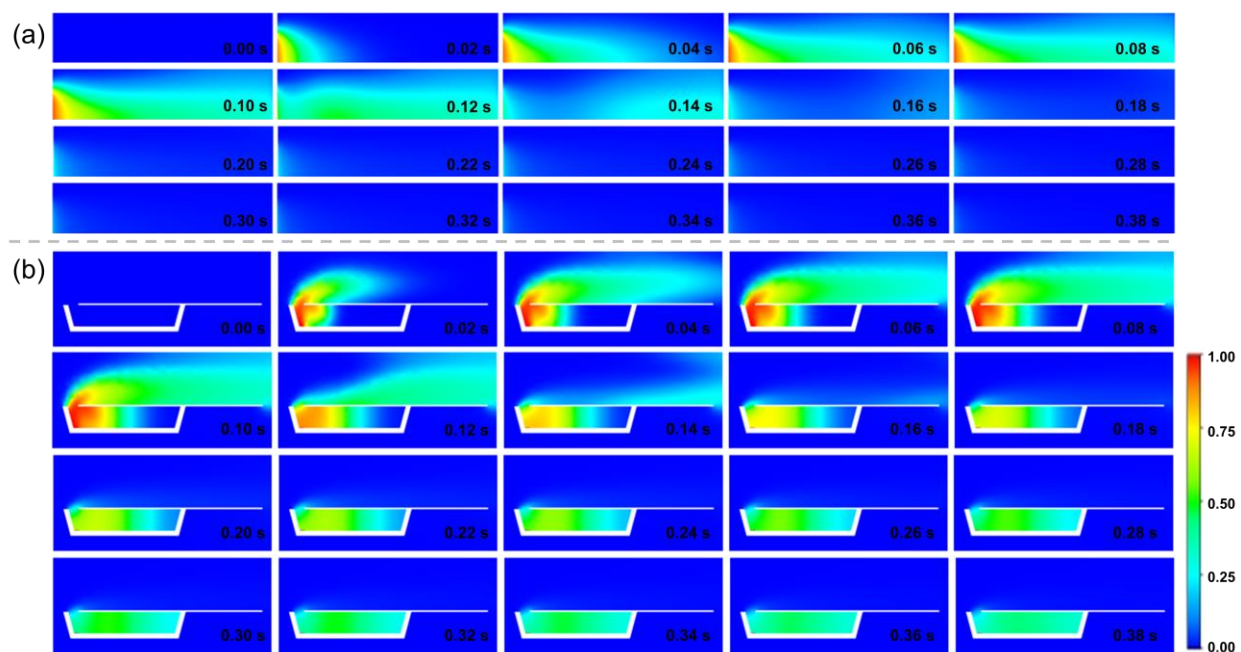


Figure S11. MoO_3 concentration evolution in the flipped APCVD growth process. (a) top view, (b) cross-sectional view.

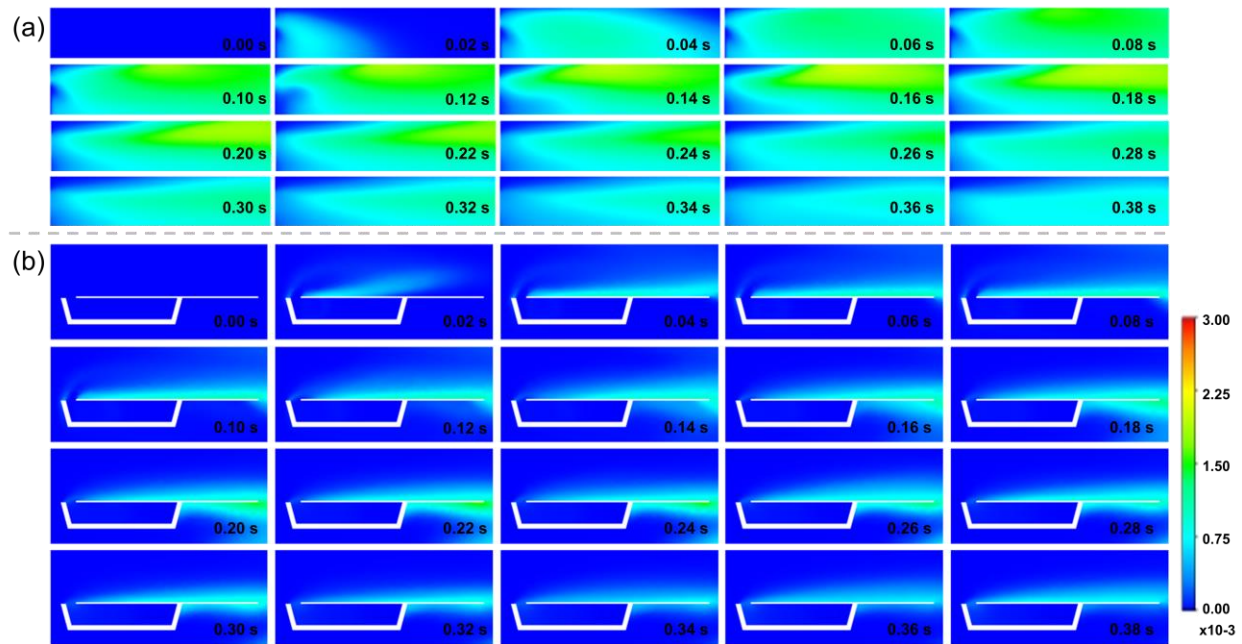


Figure S12. MoSe₂ concentration evolution in the flipped APCVD growth process. (a) top view, (b) cross-sectional view.

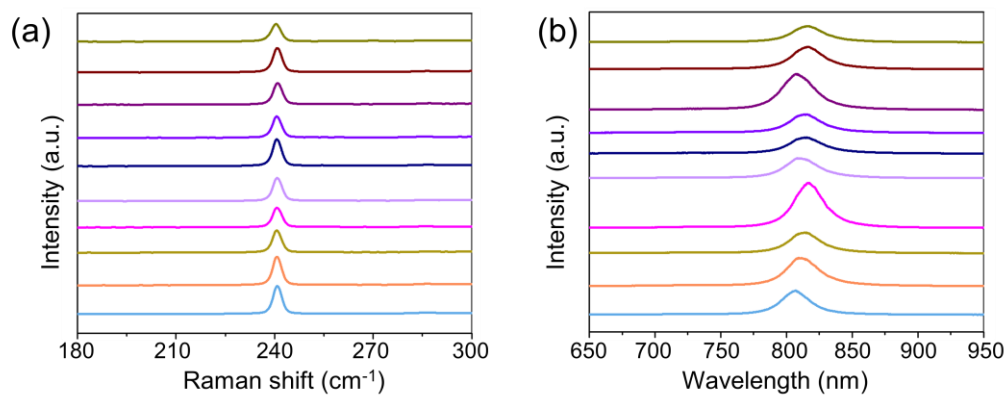


Figure S13. 10 Random Raman and PL spectra of MoSe₂ film obtained by the evolved setup.

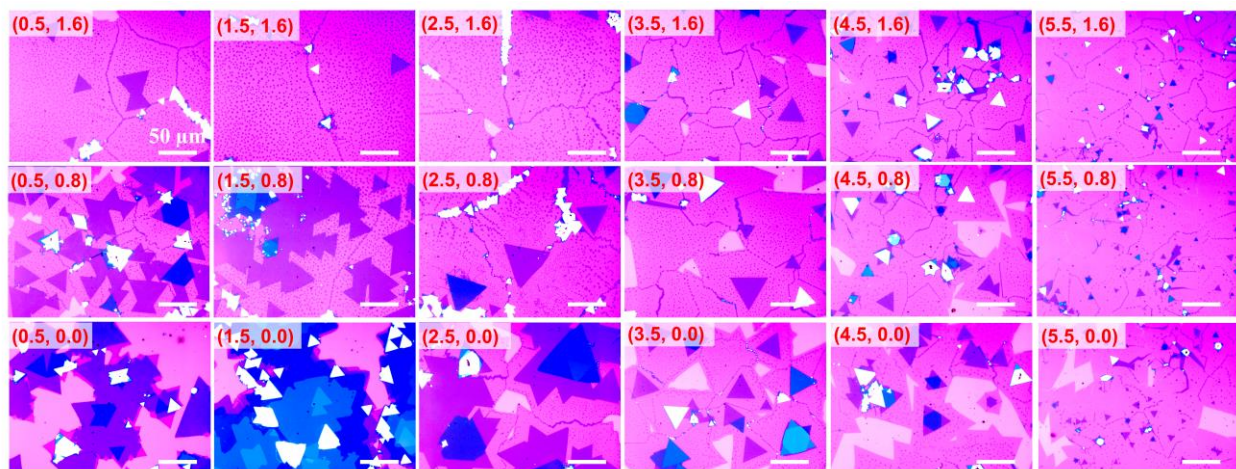


Figure S14. The detailed morphology distribution over the substrate using the evolved APCVD.

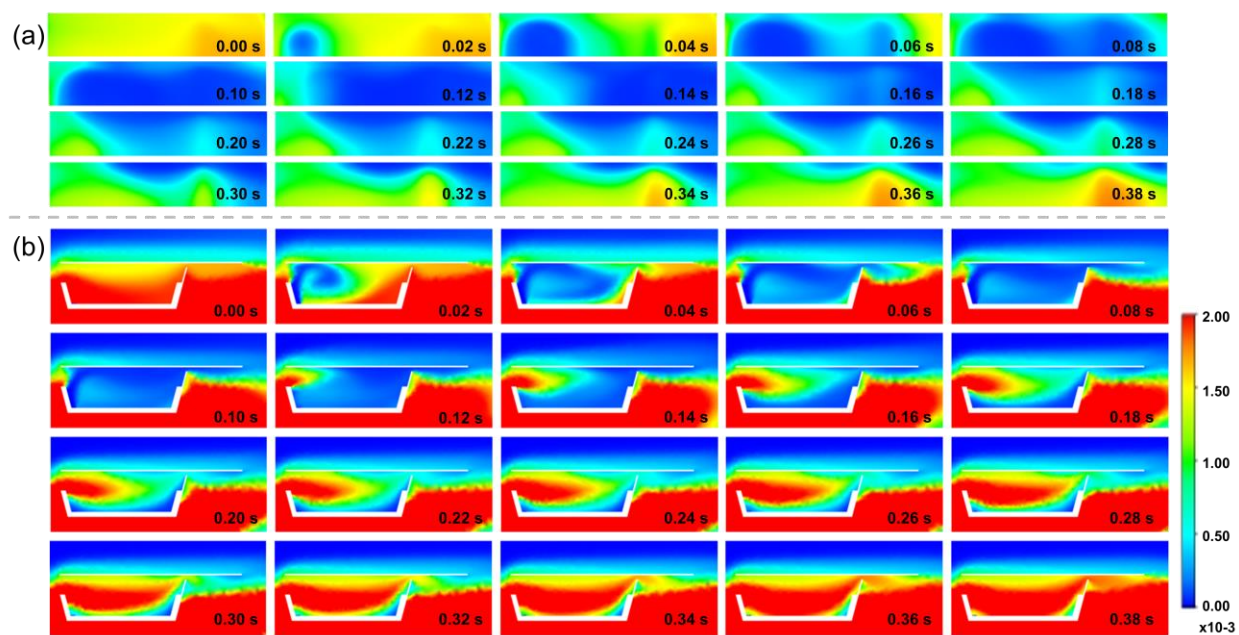


Figure S15. Se concentration evolution in the evolved APCVD growth process. (a) top view, (b) cross-sectional view.

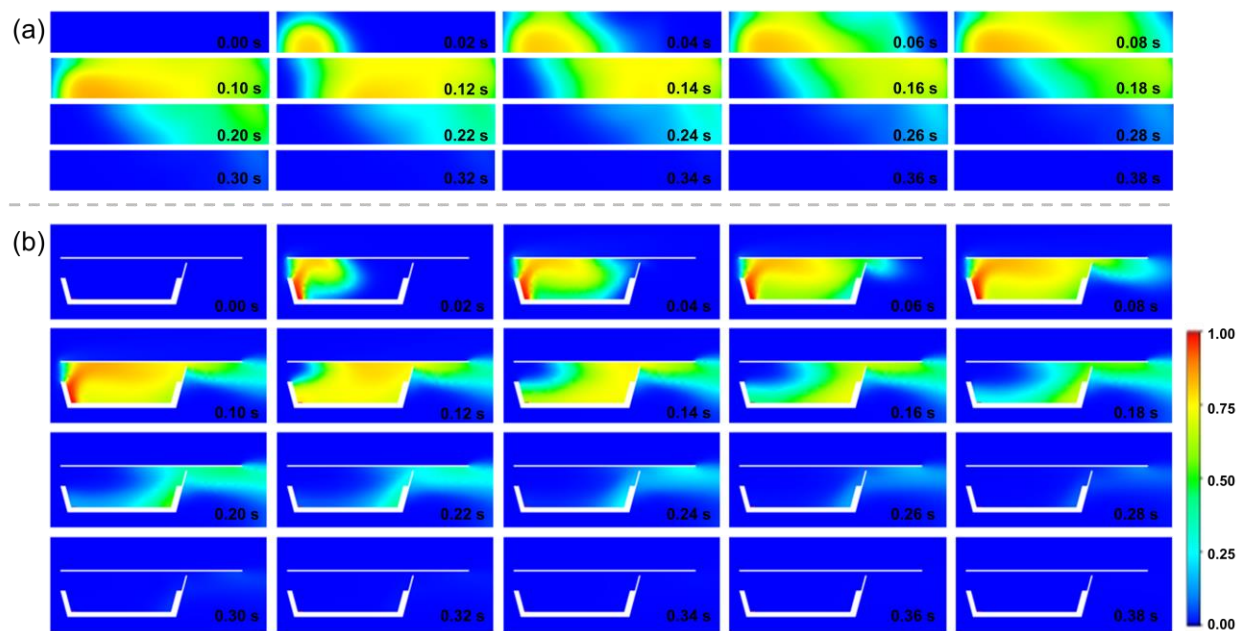


Figure S16. MoO_3 concentration evolution in the evolved APCVD growth process. (a) top view, (b) cross-sectional view.

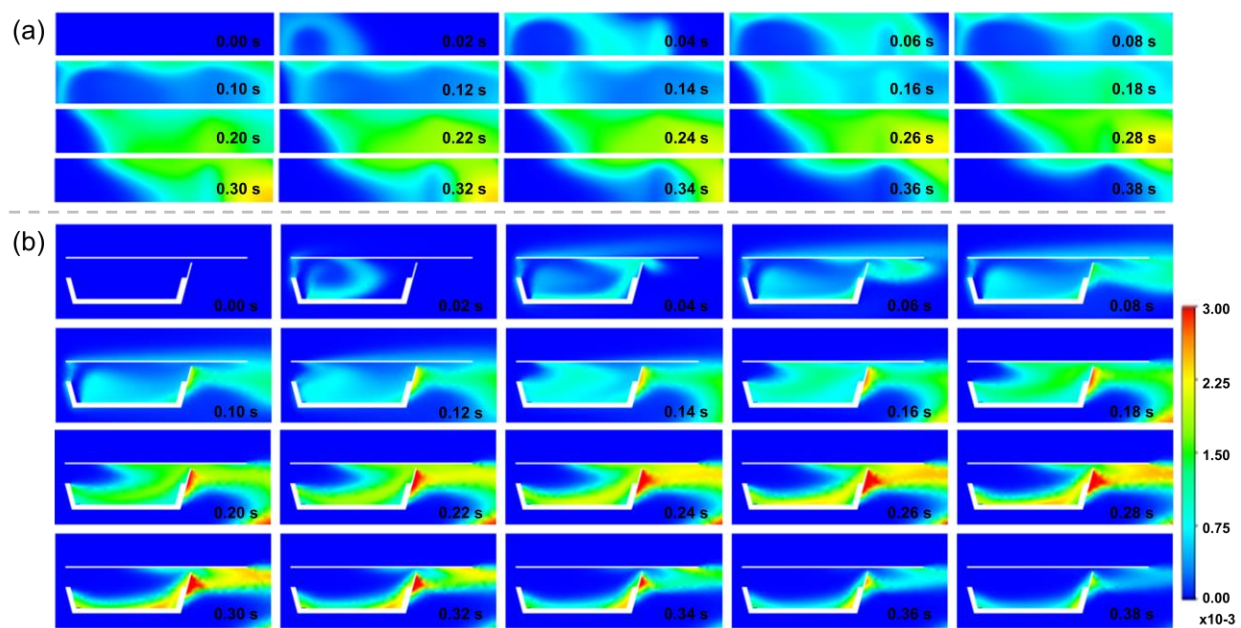


Figure S17. MoSe_2 concentration evolution in the evolved APCVD growth process. (a) top view, (b) cross-sectional view.

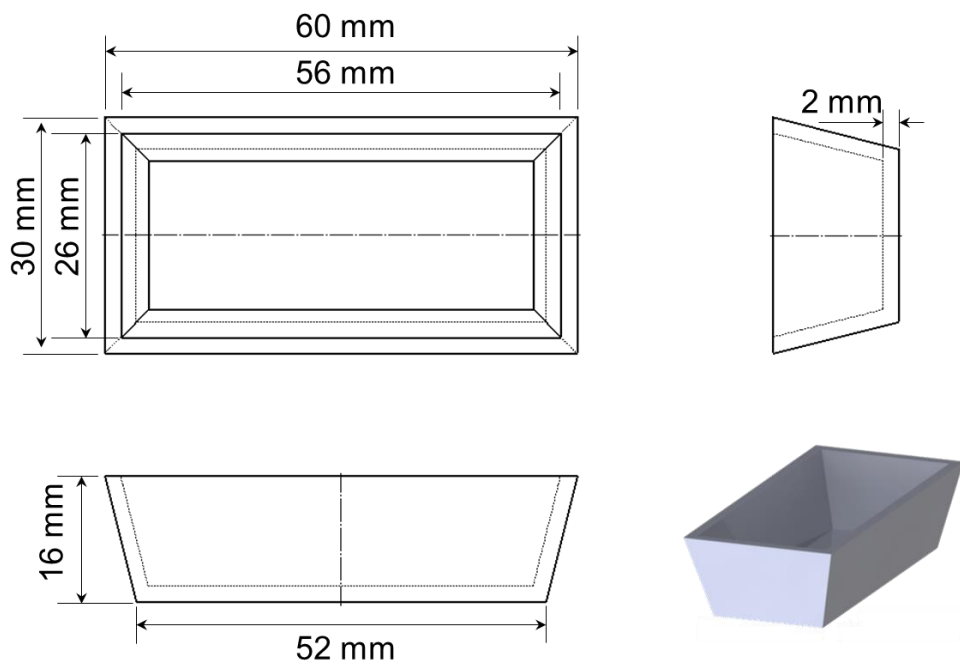


Figure S18. The structure and dimensions of the MoO_3 crucible.